## REPLACEMENT CLAIMS

5. (amended) The method of claim 1 wherein said second oxide layer is formed to at least about 60% of a targeted thickness of said second oxide layer.

20. (amended) The mathod of claim 16 wherein said second oxide layer is formed to at least about 60% of a targeted thickness of said second oxide layer.

35. (amended) The method of claim 31 wherein said second oxide layer is formed to at least about 60% of a targeted thickness of said second oxide layer.